

**Silicon PNP Power Transistors**

**2SB595**

**DESCRIPTION**

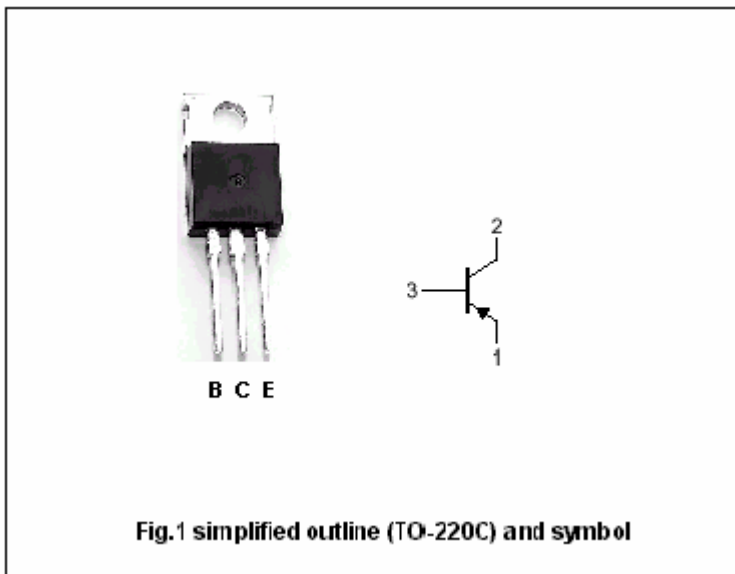
- With TO-220C package
- Complement to type 2SD525
- High breakdown voltage : $V_{CE0}=-100V$
- Low collector saturation voltage  
:  $V_{CE(sat)}=-2.0V(Max)$

**APPLICATIONS**

- Power amplifier applications
- Recommend for 30W high fidelity audio frequency amplifier output stage

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings( $T_c=25^\circ C$ )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-100	V
$V_{CEO}$	Collector-emitter voltage	Open base	-100	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-5	A
$I_E$	Emitter current		-5	A
$I_B$	Base current		-4	A
$P_C$	Collector power dissipation	$T_c=25^\circ C$	40	W
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-55~150	$^\circ C$

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA; I <sub>B</sub> =0	-100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-10mA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A; I <sub>B</sub> =-0.4 A			-2.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-4A; V <sub>CE</sub> =-5V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V	40		240	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-4A; V <sub>CE</sub> =-5V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V		5		MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz		270		pF

◆ h<sub>FE-1</sub> classifications

R	O	Y
40-80	70-140	120-240

PACKAGE OUTLINE

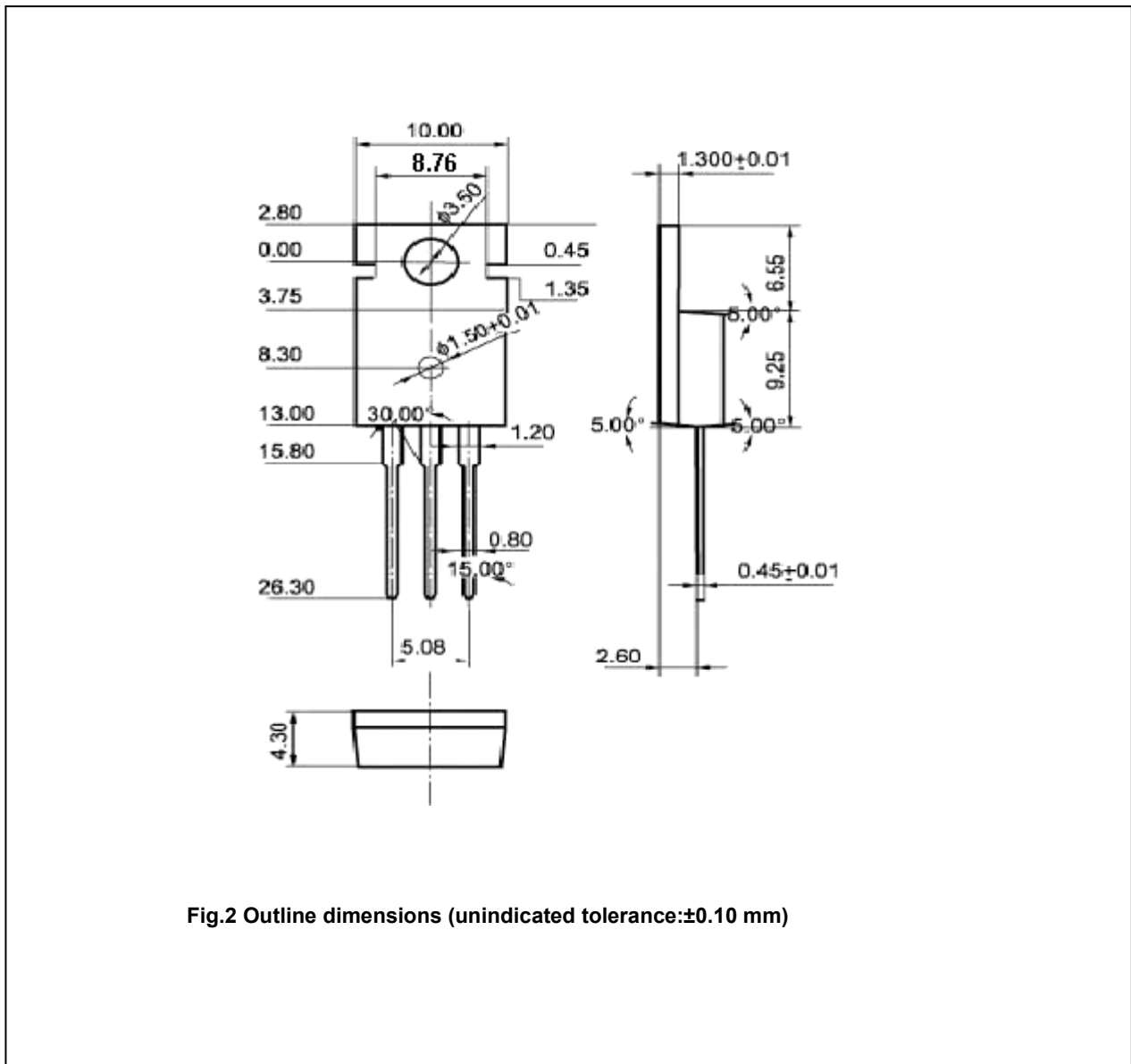


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)

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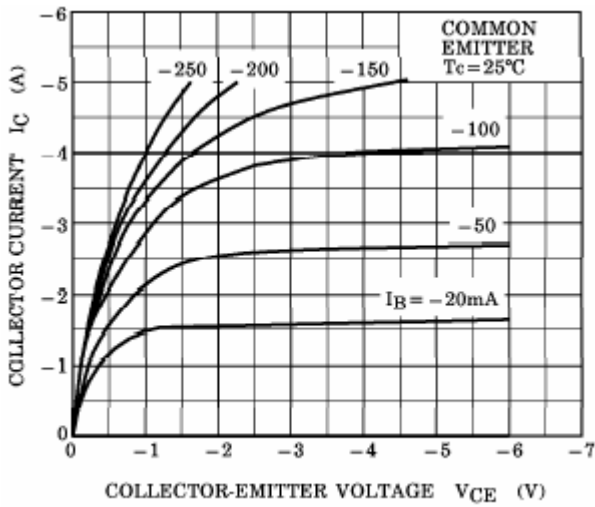


Fig.3 Static Characteristic

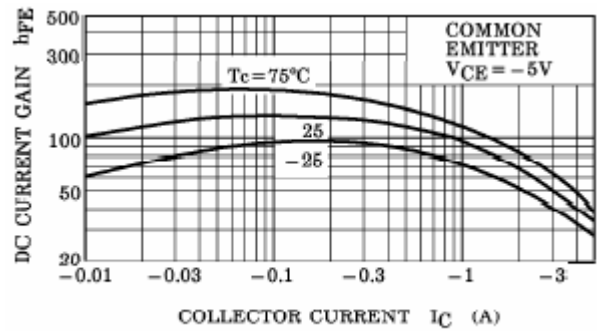


Fig.4 DC current Gain

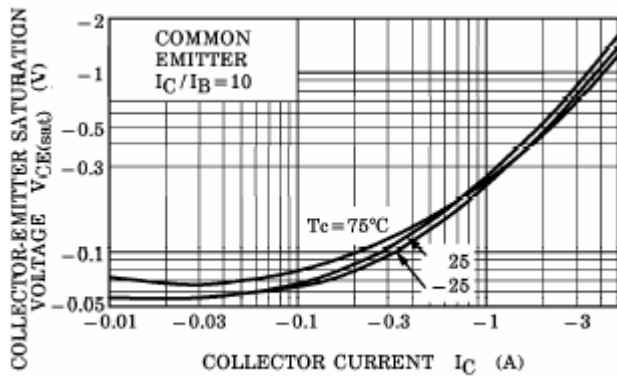


Fig.5 Collector-Emitter Saturation Voltage

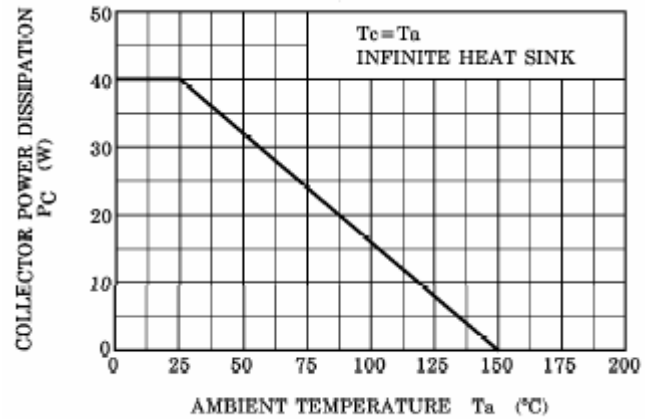


Fig.6 Power Derating

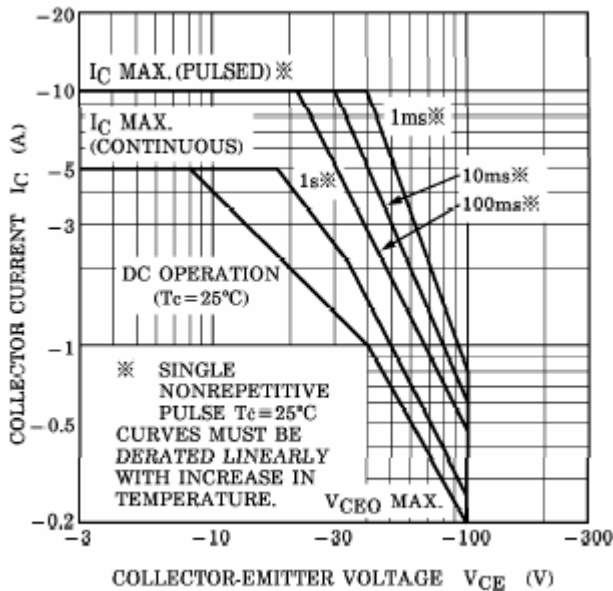


Fig.7 Safe Operating Area